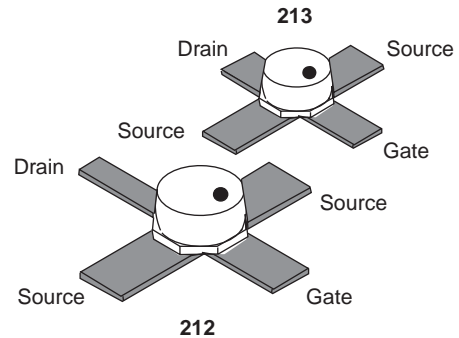


### Features

- Low Noise Figure, 1.55 dB @ 4 GHz
- High Associated Gain, 13 dB @ 4 GHz
- High MAG, > 15 dB @ 4 GHz
- 0.7  $\mu\text{m}$  Ti/Pd/Au Gates
- Passivated Surface
- Low Cost Metal Ceramic Package
- Available with Two Lead Lengths
- Available in Tape and Reel Packaging



### Description

The AFP02N8-212, 213 are general purpose packaged PHEMT chips that have excellent gain and noise performance through X band, making them suitable for a wide range of commercial applications. The devices employ 0.7  $\mu\text{m}$  Ti/Pd/Au gates and surface passivation to ensure a rugged, reliable part. Available in metal ceramic packages with a choice of two lead lengths. The components are also available in tape and reel and are ready for automatic insertion equipment.

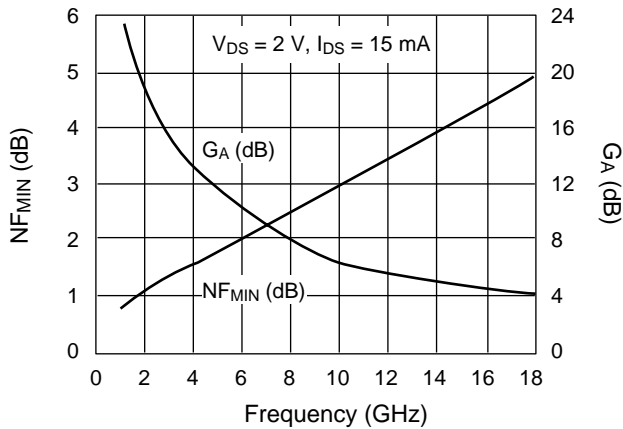
### Absolute Maximum Ratings

Characteristic	Value
Drain to Source Voltage ( $V_{DS}$ )	6 V
Gate to Source Voltage ( $V_{GS}$ )	-3 V
Drain Current ( $I_{DS}$ )	$I_{DSS}$
Gate Current ( $I_{GS}$ )	10 $\mu\text{A}$
Total Power Dissipation ( $P_T$ )	300 mW
Storage Temperature ( $T_{ST}$ )	-65 to +150°C
Channel Temperature ( $T_{CH}$ )	175°C

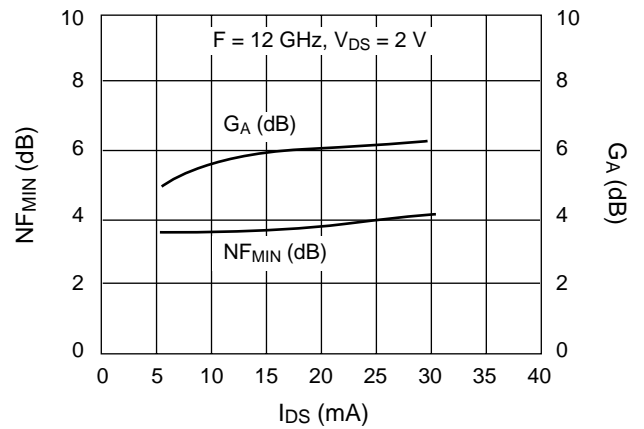
### Electrical Specifications at 25°C

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Saturated Drain Current ( $I_{DSS}$ )	$V_{DS} = 2 \text{ V}, V_{GS} = 0 \text{ V}$	25.0	55.0	90.0	mA
Transconductance (gm)	$V_{DS} = 2 \text{ V}, I_{DS} = 15 \text{ mA}$	30.0	45.0		mS
Pinch-off Voltage ( $V_P$ )	$V_{DS} = 2 \text{ V}, I_{DS} = 0.3 \text{ mA}$	-0.4	-1.2	-2.0	V
Gate to Source Breakdown Voltage ( $V_{bgs}$ )	$I_{GS} = -200 \mu\text{A}$	-6.0	8.0		V
Noise Figure (NF)	$V_{DS} = 2 \text{ V}, I_{DS} = 15 \text{ mA}, F = 4 \text{ GHz}$		1.55	2.0	dB
Associated Gain ( $G_A$ )		12.0	13.2		dB

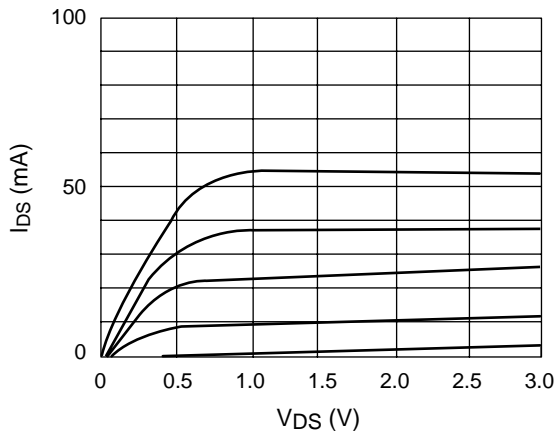
### Typical Performance Data



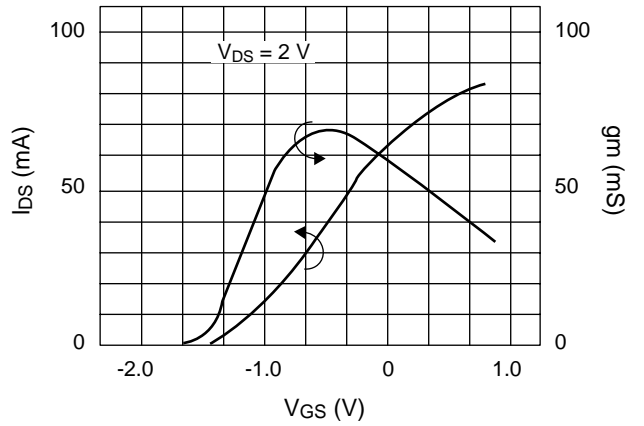
RF Minimum Noise Figure ( $NF_{MIN}$ ) and Associated Gain ( $G_A$ ) vs. Frequency (GHz)



RF Minimum Noise Figure ( $NF_{MIN}$ ) and Associated Gain ( $G_A$ ) vs. Drain Current ( $I_{DS}$ )



DC Drain Current ( $I_{DS}$ ) vs. Drain Voltage ( $V_{DS}$ ) as a Function of Gate to Source Voltage ( $V_{GS}$ )



DC Drain Current ( $I_{DS}$ ) and Transconductance ( $g_m$ ) vs. Gate to Source Voltage ( $V_{GS}$ )

### Typical Noise Parameters

( $V_{DS} = 2\text{ V}$ ,  $I_{DS} = 15\text{ mA}$ )

Freq. (GHz)	$NF_{MIN}$ (dB)	$\Gamma_{opt}$		$R_N/50$	$G_A$ (dB)
		Mag.	Ang.		
1	0.75	0.84	25.40	0.12	23.50
2	1.10	0.72	50.20	0.23	18.00
4	1.55	0.54	99.00	0.23	13.20
6	2.00	0.43	145.40	0.15	10.20
8	2.50	0.39	-171.80	0.16	8.10
10	3.00	0.39	-133.60	0.32	6.51
12	3.50	0.43	-100.10	0.66	5.82
14	4.00	0.48	-71.10	1.16	5.20
16	4.50	0.55	-45.90	1.77	4.51
18	5.00	0.60	-23.30	2.38	4.10

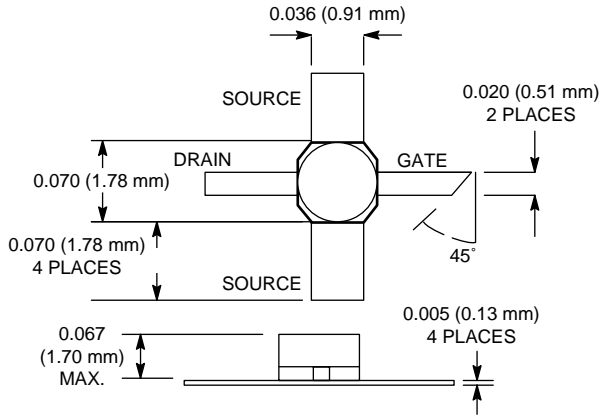
Typical S-Parameters ( $V_{DS} = 2\text{ V}$ ,  $I_{DS} = 10\text{ mA}$ )

Freq. (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>		k	S <sub>21</sub> (dB)	MAG/MSG (dB)
	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.			
2	0.907	-62.79	3.464	127.20	0.064	50.72	0.668	-34.68	0.28	10.79	17.33
3	0.838	-90.38	3.023	105.25	0.081	34.37	0.624	-48.83	0.41	9.61	15.72
4	0.783	-111.85	2.621	86.99	0.089	21.93	0.597	-60.61	0.56	8.37	14.69
5	0.736	-130.94	2.336	71.00	0.940	11.76	0.578	-69.70	0.71	7.37	13.95
6	0.678	-148.78	2.121	57.32	0.097	4.01	0.541	-75.33	0.93	6.53	13.40
7	0.646	-169.88	1.963	41.01	0.100	-6.30	0.529	-85.97	1.05	5.86	11.60
8	0.623	170.99	1.757	25.78	0.094	-16.83	0.498	-96.93	1.35	4.90	9.21
9	0.608	156.18	1.586	13.51	0.085	-22.69	0.478	-106.72	1.72	4.01	7.77
10	0.588	144.21	1.507	2.06	0.082	-21.86	0.489	-116.05	1.88	3.56	7.23
11	0.575	128.33	1.460	-10.69	0.087	-23.31	0.478	-125.41	1.88	3.29	6.85
12	0.585	105.80	1.400	-24.70	0.092	-27.09	0.448	-131.83	1.87	2.92	6.45
13	0.609	88.23	1.286	-38.34	0.092	-31.27	0.412	-143.23	2.02	2.19	5.68
14	0.638	80.34	1.209	-49.37	0.099	-31.92	0.413	-159.92	1.85	1.65	5.54
15	0.647	70.32	1.154	-61.37	0.108	-36.23	0.433	-175.05	1.68	1.24	5.48
16	0.634	57.45	1.114	-74.60	0.117	-42.67	0.457	170.14	1.60	0.94	5.24
17	0.644	43.29	1.058	-87.78	0.126	-50.03	0.440	154.96	1.58	0.49	4.77
18	0.676	29.15	0.988	-100.88	0.133	-58.17	0.410	138.93	1.55	-0.11	4.33

Typical S-Parameters ( $V_{DS} = 2\text{ V}$ ,  $I_{DS} = 30\text{ mA}$ )

Freq. (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>		k	S <sub>21</sub> (dB)	MAG/MSG (dB)
	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.			
2	0.897	-67.62	3.880	124.82	0.056	52.03	0.532	-35.74	0.35	11.78	18.41
3	0.827	-96.33	3.324	102.91	0.070	37.48	0.496	-49.61	0.51	10.43	16.77
4	0.774	-118.37	2.849	84.93	0.077	26.85	0.477	-60.94	0.68	9.09	15.68
5	0.730	-137.87	2.514	69.09	0.083	18.48	0.465	-69.52	0.84	8.01	14.81
6	0.676	-156.27	2.270	55.39	0.087	12.39	0.436	-74.37	1.07	7.12	12.53
7	0.651	-177.55	2.079	39.24	0.091	3.17	0.428	-84.64	1.18	6.36	11.02
8	0.634	163.71	1.850	24.48	0.088	-5.10	0.401	-95.45	1.46	5.34	9.22
9	0.622	149.23	1.669	12.62	0.083	-8.69	0.384	-105.44	1.77	4.45	7.93
10	0.603	137.25	1.582	1.26	0.087	-7.85	0.396	-114.72	1.81	3.98	7.39
11	0.595	121.36	1.526	-11.54	0.096	-11.14	0.385	-123.78	1.74	3.67	7.02
12	0.611	99.49	1.450	-25.54	0.105	-17.16	0.355	-129.74	1.66	3.23	6.64
13	0.636	82.95	1.324	-38.78	0.108	-23.35	0.316	-141.03	1.75	2.44	5.87
14	0.666	75.34	1.247	-49.46	0.117	-26.77	0.314	-158.74	1.58	1.92	5.79
15	0.673	65.30	1.193	-61.23	0.128	-32.92	0.335	-175.09	1.45	1.53	5.72
16	0.660	52.28	1.152	-74.33	0.138	-41.04	0.359	169.60	1.41	1.23	5.42
17	0.672	38.51	1.087	-87.24	0.146	-49.76	0.340	153.84	1.41	0.73	4.91
18	0.705	25.05	1.014	-99.87	0.152	-58.48	0.308	136.82	1.39	0.12	4.53

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